

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant(s): Hussein I. Hanafi, et al.

Examiner: Unassigned

Serial No: To be assigned

Art Unit: Unassigned

Filed: Herewith

Docket: YOR2002018US2 (15790A)

For: LOW RESISTANCE T-GATE MOSFET
DEVICE USING A DAMASCENE GATE
PROCESS AND AN INNOVATIVE
OXIDE REMOVAL ETCH

Dated: September 11, 2003

Commissioner for Patents
United States Patent and Trademark Office
P.O. Box 1450
Alexandria, VA 22313-1450

PRELIMINARY AMENDMENT

Sir:

In connection with filing the above-identified patent application under 37
C.F.R. §1.53(b), applicants submit the following amendments and remarks for entry of
record in the above-identified patent application.

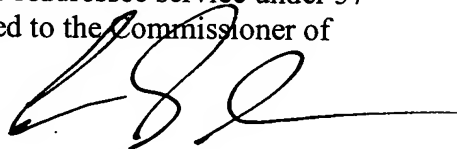
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United States Postal Service Express Mail Post Office to Addressee service under 37
C.F.R. §1.10 on the date indicated above and is addressed to the Commissioner of
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Dated: September 11, 2003



Leslie S. Szivos, Ph.D.